

PATENT ASSIGNMENT

Electronic Version v1.1

Stylesheet Version v1.1

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
Micron Technology, Inc.	06/09/2009
RECEIVING PARTY DATA	
Name:	MOSAID Technologies Incorporated
Street Address:	11 Hines Road, Suite 203
City:	Ottawa, Ontario
State/Country:	CANADA
Postal Code:	K2K 2X1
PROPERTY NUMBERS Total: 1	
Property Type	Number
Application Number:	11511652
CORRESPONDENCE DATA	
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ATTORNEY DOCKET NUMBER:	MTI-31043-AAA
NAME OF SUBMITTER:	Jere L. Polmatier
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ASSIGNMENT OF PATENT RIGHTS

Definitions

"Assignor" is Micron Technology, Inc., a Delaware corporation with offices at 8000 South Federal Way, Boise, ID, USA.

"Assignee" is MOSAID Technologies Incorporated, a Canadian company, with an office located at 11 Hines Road, Suite 203, Ottawa, Ontario, Canada K2K 2X1.

"The Patents" are the patents and patent applications identified in Schedule A below, including, without limitation, all parents, divisionals, continuations, continuations-in-part, reissues, and reexaminations thereof and all pending applications therefore, and all foreign counterparts thereof and all pending applications therefor, and any patents resulting therefrom.

Covenants

Assignor, for good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged, hereby sells, assigns, and transfers to Assignee its entire right, title and interest in and to The Patents.

Assignor hereby sells, assigns, and transfers to Assignee all claims for damages and all remedies arising out of any violation of the rights assigned hereby that may have accrued prior to the date of this Assignment, or may accrue hereafter, including, but not limited to, the right to bring suit and to collect and retain damages for past infringement of The Patents.

Assignor hereby authorizes and requests the Commissioner of Patents of the United States, and any other official of the United States and any country foreign to the United States whose duty it is to issue or record patents, to issue The Patents to Assignee and to record assignment of The Patents to Assignee.

This Assignment shall be binding on the heirs, assigns, representatives, and successors of Assignor and shall extend to and inure to the benefit of the successors and assigns of the Assignee.

Agreed to by:

Micron Technology, Inc.

Signed: Roderic W. Lewis

Roderic W. Lewis

Vice President of Legal Affairs, and General Counsel

Date: 6/9/2009

Notarization

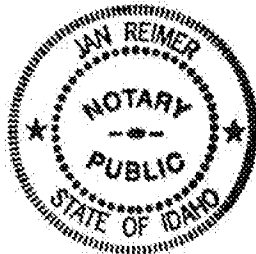
State of Idaho

County of Ada

On 6/9/2009, before me, Jan Reimer, personally appeared the

above-named Roderic W. Lewis, who executed this Assignment in my presence and

acknowledged to me that he did so of his own free will and in his authorized capacity for the purposes set forth herein.



Signed: Jan Reimer

My commission expires: 9/11/2013

Schedule A

Patents and Applications

PatentNo	SerialNo	Country	MatterStatus	Title	FileDate	IssueDate
6,218,237	08/582,385	US	Issued	METHOD OF FORMING A CAPACITOR AND A CAPACITOR CONSTRUCTION	1/3/1996	4/17/2001
6,900,496	08/886,388	US	Issued	CAPACITOR CONSTRUCTIONS	7/1/1997	5/31/2005
6,214,687	09/251,387	US	Issued	METHOD OF FORMING A CAPACITOR AND A CAPACITOR CONSTRUCTION	2/17/1999	4/10/2001
6,395,602	09/779,219	US	Issued	METHOD OF FORMING A CAPACITOR	2/7/2001	5/28/2002
6,762,450	09/876,102	US	Issued	METHOD OF FORMING A CAPACITOR AND A CAPACITOR CONSTRUCTION	6/6/2001	7/13/2004
6,752,912	09/384,740	US	Issued	DIRECTIONAL DEPOSITION USING LASER IONIZATION AND DC FIELD	8/27/1999	6/22/2004
7,011,733	10/858,307	US	Issued	DIRECTIONAL DEPOSITION USING LASER IONIZATION AND DC FIELD	6/1/2004	3/14/2006
5,946,594	08/581,765	US	Issued	CHEMICAL VAPOR DEPOSITION OF TITANIUM FROM TITANIUM TETRACHLORIDE AND HYDROCARBON REACTANTS	1/2/1996	8/31/1999
6,184,136	09/292,993	US	Issued	CHEMICAL VAPOR DEPOSITION OF TITANIUM FROM TITANIUM TETRACHLORIDE AND HYDROCARBON REACTANTS	4/16/1999	2/6/2001
6,340,637	09/730,038	US	Issued	CHEMICAL VAPOR DEPOSITION OF TITANIUM FROM TITANIUM TETRACHLORIDE AND HYDROCARBON REACTANTS	12/5/2000	1/22/2002

6,653,234	10/011,134	US	Issued	CHEMICAL VAPOR DEPOSITION OF TITANIUM FROM TITANIUM TETRACHLORIDE AND HYDROCARBON REACTANTS	12/7/2001	11/25/2003
6,977,225	10/706,244	US	Issued	CHEMICAL VAPOR DEPOSITION OF TITANIUM FROM TITANIUM TETRACHLORIDE AND HYDROCARBON REACTANTS	11/12/2003	12/20/2005
7,268,078	11/298,978	US	Issued	CHEMICAL VAPOR DEPOSITION OF TITANIUM FROM TITANIUM TETRACHLORIDE AND HYDROCARBON REACTANTS	12/9/2005	9/11/2007
6,436,246	08/788,980	US	Issued	COLLIMATED SPUTTER DEPOSITION MONITOR USING SHEET RESISTANCE	1/27/1997	8/20/2002
6,436,247	09/932,233	US	Issued	COLLIMATED SPUTTER DEPOSITION MONITOR USING SHEET RESISTANCE	8/17/2001	8/20/2002
5,518,948	08/534,572	US	Issued	CUP-SHAPED DRAM CAPACITOR HAVING AN INWARDLY OVERHANGING LIP AND METHOD OF MANUFACTURING SAME	9/27/1995	5/21/1996
6,001,189	08/724,578	US	Issued	METHOD FOR REDUCING GASEOUS SPECIES OF CONTAMINATION IN WET PROCESSES	9/30/1996	12/14/1999
6,521,049	09/327,152	US	Issued	METHOD FOR REDUCING GASEOUS SPECIES OF CONTAMINATION IN WET PROCESSES	6/7/1999	2/18/2003
6,866,049	10/346,980	US	Issued	DEVICE ADDRESSING GAS CONTAMINATION IN A WET PROCESS (AS AMENDED)	1/16/2003	3/15/2005
	11/038,451	US	Abandoned	DEVICE AND METHOD ADDRESSING GAS CONTAMINATION IN A WET PROCESS	1/19/2005	
6,271,590	09/138,811	US	Issued	GRADED LAYER FOR USE IN SEMICONDUCTOR CIRCUITS AND METHOD FOR MAKING SAME	8/21/1998	8/7/2001
6,451,658	09/887,612	US	Issued	GRADED LAYER FOR USE IN SEMICONDUCTOR CIRCUITS AND METHOD FOR MAKING SAME	6/22/2001	9/17/2002
6,545,356	10/051,768	US	Issued	GRADED LAYER FOR USE IN SEMICONDUCTOR CIRCUITS AND METHOD FOR MAKING SAME	1/18/2002	4/8/2003

5,742,555	08/700,234	US	Issued	A METHOD OF ANTI-FUSE REPAIR	8/20/1996	4/21/1998
5,978,248	09/030,130	US	Issued	A METHOD OF ANTI-FUSE REPAIR	2/25/1998	11/2/1999
6,836,000	09/389,072	US	Abandoned	A METHOD OF ANTI-FUSE REPAIR	9/2/1999	
6,233,194	09/515,760	US	Issued	ANTI-FUSE STRUCTURE AND METHOD OF USE	3/1/2000	12/28/2004
6,515,931	09/560,498	US	Issued	A METHOD OF ANTI-FUSE REPAIR	4/27/2000	5/15/2001
7,071,534	09/845,794	US	Issued	METHOD OF ANTI-FUSE REPAIR	4/30/2001	2/4/2003
6,496,027	10/931,714	US	Issued	ANTI-FUSE STRUCTURE AND METHOD OF USE	9/1/2004	7/4/2006
6,756,805	08/916,994	US	Issued	SYSTEM FOR TESTING INTEGRATED CIRCUIT DEVICES	8/21/1997	12/17/2002
6,930,503	10/295,499	US	Issued	SYSTEM FOR TESTING INTEGRATED CIRCUIT DEVICES	11/15/2002	6/29/2004
	10/835,945	US	Issued	SYSTEM FOR TESTING INTEGRATED CIRCUIT DEVICES	4/30/2004	8/16/2005
	11/200,372	US	Abandoned	SYSTEM FOR TESTING INTEGRATED CIRCUIT DEVICES	8/9/2005	
	11/731,930	US	Abandoned	METHOD FOR FORMING A SYSTEM TO TEST INTEGRATED CIRCUIT DEVICES	4/2/2007	
6,063,656	08/844,512	US	Issued	PRISM AND HALF MOON CELL CAPACITORS	4/18/1997	5/16/2000
6,153,903	09/204,526	US	Issued	PRISM AND HALF MOON CELL CAPACITORS	12/3/1998	11/28/2000
6,225,159	09/426,965	US	Issued	CELL CAPACITORS, MEMORY CELLS, MEMORY ARRAYS AND METHOD OF FABRICATION	10/26/1999	5/1/2001
6,420,270	09/645,906	US	Issued	METHOD OF PRODUCING AN ETCH PATTERN	8/25/2000	7/16/2002
6,429,475	09/645,251	US	Issued	CELL CAPACITORS, MEMORY CELLS, MEMORY ARRAYS, AND METHOD OF FABRICATION	8/24/2000	8/6/2002
6,043,119	08/906,213	US	Issued	CONCAVE CAPACITOR AND METHOD OF MAKING	8/4/1997	3/28/2000
6,459,116	09/283,606	US	Issued	CAPACITOR STRUCTURE	4/1/1999	10/1/2002
6,682,984	09/535,483	US	Issued	METHOD OF MAKING A CONCAVE CAPACITOR	3/24/2000	1/27/2004
6,787,839	10/145,435	US	Issued	CAPACITOR STRUCTURE	5/14/2002	9/7/2004
6,740,923	10/145,250	US	Issued	CAPACITOR STRUCTURE	5/14/2002	5/25/2004
6,885,542	10/932,503	US	Issued	CAPACITOR STRUCTURE	9/2/2004	4/26/2005
	11/079,924	US	Abandoned	CAPACITOR STRUCTURE	3/14/2005	

6,280,793	08/752,834	US	Issued	ELECTROSTATIC METHOD AND APPARATUS FOR VAPORIZING PRECURSORS AND SYSTEM FOR USING SAME	11/20/1996	8/28/2001
5,666,306	08/706,662	US	Issued	MULTIPLICATION OF STORAGE CAPACITANCE IN MEMORY CELLS USING THE MILLER EFFECT	9/6/1996	9/9/1997
5,835,403	08/879,908	US	Issued	MULTIPLICATION OF STORAGE CAPACITANCE IN MEMORY CELLS USING THE MILLER EFFECT	6/20/1997	11/10/1998
5,995,410	09/123,634	US	Issued	MULTIPLICATION OF STORAGE CAPACITANCE IN MEMORY CELLS USING THE MILLER EFFECT	7/28/1998	11/30/1999
	08/749,001	US	Abandoned	A SOLVENT PREWET AND METHOD AND APPARATUS TO DISPENSE THE SOLVENT PREWET	11/14/1996	
6,147,010	08/974,015	US	Issued	A SOLVENT PREWET AND METHOD AND APPARATUS TO DISPENSE THE SOLVENT PREWET	11/19/1997	11/14/2000
6,284,676	09/650,876	US	Issued	SOLVENT PREWET AND METHOD AND APPARATUS TO DISPENSE THE SOLVENT PREWET	8/30/2000	9/4/2001
6,579,471	09/942,157	US	Issued	A SOLVENT PREWET AND METHOD TO DISPENSE THE SOLVENT PREWET	8/29/2001	6/17/2003
6,758,908	09/941,476	US	Issued	SOLVENT PREWET AND METHOD AND APPARATUS TO DISPENSE THE SOLVENT PREWET	8/29/2001	7/6/2004
6,884,462	10/836,053	US	Issued	SOLVENT PREWET AND METHOD TO DISPENSE THE SOLVENT PREWET	4/30/2004	4/26/2005
	11/114,791	US	Abandoned	SOLVENT PREWET AND METHOD TO DISPENSE THE SOLVENT PREWET	4/26/2005	
6,328,803	08/805,018	US	Issued	METHOD AND APPARATUS FOR CONTROLLING RATE OF PRESSURE CHANGE IN A VACUUM PROCESS CHAMBER	2/21/1997	12/11/2001
6,384,001	08/808,014	US	Issued	DILUTE CLEANING COMPOSITION (AS AMENDED)	3/3/1997	5/7/2002
6,136,767	09/196,661	US	Issued	DILUTE COMPOSITION CLEANING METHOD (AS AMENDED)	11/19/1998	10/24/2000

6,313,048	09/325,375	US	Issued	DILUTE CLEANING COMPOSITION AND METHOD FOR USING SAME	6/4/1999	11/6/2001
6,596,647	09/929,640	US	Issued	DILUTE CLEANING COMPOSITION AND METHOD FOR USING SAME	8/14/2001	7/22/2003
6,841,525	09/935,234	US	Issued	DILUTE CLEANING COMPOSITION AND METHOD FOR USING SAME	8/22/2001	1/11/2005
	11/025,687	US	Abandoned	DILUTE CLEANING COMPOSITION AND METHOD FOR USING SAME	12/29/2004	
6,273,100	09/141,384	US	Issued	SUBMERGED WAFER SCRUBBER	8/27/1998	8/14/2001
6,269,511	09/679,806	US	Issued	SURFACE CLEANING APPARATUS AND METHOD	10/4/2000	8/7/2001
	08/916,834	US	Abandoned	INTEGRATED CLEANER WITH SCRUBBER AND METHOD OF USE	8/22/1997	
6,358,325	09/468,022	US	Issued	POLYSILICON-SILICON DIOXIDE CLEANING PROCESS PERFORMED IN AN INTEGRATED CLEANER WITH SCRUBBER	12/20/1999	3/19/2002
5,822,258	08/851,416	US	Issued	CIRCUIT AND METHOD FOR TESTING A MEMORY DEVICE	5/5/1997	10/13/1998
5,943,276	09/031,973	US	Issued	CIRCUIT AND METHOD FOR TESTING A MEMORY DEVICE	2/26/1998	8/24/1999
6,134,162	09/360,952	US	Issued	CIRCUIT AND METHOD FOR TESTING A MEMORY DEVICE WITH A CELL PLATE GENERATOR HAVING A VARIABLE CURRENT	7/27/1999	10/17/2000
6,327,200	09/640,610	US	Issued	CIRCUIT AND METHOD FOR TESTING A MEMORY DEVICE	8/17/2000	12/4/2001
6,359,817	09/640,611	US	Issued	CIRCUIT AND METHOD FOR TESTING A MEMORY DEVICE	8/17/2000	3/19/2002
6,714,468	10/099,220	US	Issued	CIRCUIT AND METHOD FOR TESTING A MEMORY DEVICE WITH A CELL PLATE GENERATOR HAVING A VARIABLE CURRENT	3/13/2002	3/30/2004

	08/903,453	US	Abandoned	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS	7/29/1997	
6,794,255	09/258,467	US	Issued	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS	2/26/1999	9/21/2004
6,731,531	09/650,553	US	Issued	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS	8/30/2000	5/4/2004
	11/235,963	US	Abandoned	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS	9/27/2005	
6,025,232	08/968,085	US	Issued	METHODS OF FORMING FIELD EFFECT TRANSISTORS AND RELATED FIELD EFFECT TRANSISTOR CONSTRUCTIONS	11/12/1997	2/15/2000
6,400,002	09/490,257	US	Issued	METHODS OF FORMING FIELD EFFECT TRANSISTORS AND RELATED FIELD EFFECT TRANSISTOR CONSTRUCTIONS	1/24/2000	6/4/2002
6,413,823	09/460,253	US	Issued	METHODS OF FORMING FIELD EFFECT TRANSISTORS	12/13/1999	7/2/2002
6,344,382	09/494,835	US	Issued	METHODS OF FORMING FIELD EFFECT TRANSISTORS AND RELATED FIELD EFFECT TRANSISTOR CONSTRUCTIONS	1/31/2000	2/5/2002
6,482,691	09/494,974	US	Issued	METHOD OF FORMING FIELD EFFECT TRANSISTORS AND RELATED FIELD EFFECT TRANSISTOR CONSTRUCTIONS	1/31/2000	11/19/2002
6,406,957	09/494,973	US	Issued	METHODS OF FORMING FIELD EFFECT TRANSISTORS AND RELATED FIELD EFFECT TRANSISTOR CONSTRUCTIONS	1/31/2000	6/18/2002
6,335,234	09/495,416	US	Issued	METHODS OF FORMING FIELD EFFECT TRANSISTORS AND RELATED FIELD EFFECT TRANSISTOR CONSTRUCTIONS	1/31/2000	1/1/2002
6,335,246	09/494,836	US	Issued	METHODS OF FORMING FIELD EFFECT TRANSISTORS AND RELATED FIELD EFFECT TRANSISTOR CONSTRUCTIONS	1/31/2000	1/1/2002

6,475,852	09/999,886	US	Issued	METHODS OF FORMING FIELD EFFECT TRANSISTORS AND RELATED FIELD EFFECT TRANSISTOR CONSTRUCTIONS	10/31/2001	11/5/2002
6,472,260	09/999,885	US	Issued	METHODS OF FORMING FIELD EFFECT TRANSISTORS AND RELATED FIELD EFFECT TRANSISTOR CONSTRUCTIONS	10/31/2001	10/29/2002
6,673,663	10/143,264	US	Issued	METHODS OF FORMING FIELD EFFECT TRANSISTORS AND RELATED FIELD EFFECT TRANSISTOR CONSTRUCTIONS	5/8/2002	1/6/2004
5,938,860	08/921,656	US	Issued	RETICLE CLEANING WITHOUT DAMAGING PELLICLE	8/28/1997	8/17/1999
6,165,650	09/310,521	US	Issued	RETICLE CLEANING WITHOUT DAMAGING PELLICLE	5/12/1999	12/26/2000
6,063,208	09/310,520	US	Issued	RETICLE CLEANING WITHOUT DAMAGING PELLICLE	5/12/1999	5/16/2000
6,458,216	09/543,036	US	Issued	RETICLE CLEANING WITHOUT DAMAGING PELLICLE	4/5/2000	10/1/2002
6,284,417	09/651,392	US	Issued	RETICLE CLEANING WITHOUT DAMAGING PELLICLE	8/29/2000	9/4/2001
6,395,436	09/924,636	US	Issued	RETICLE CLEANING WITHOUT DAMAGING PELLICLE	8/8/2001	5/28/2002
6,500,588	10/125,853	US	Issued	RETICLE CLEANING WITHOUT DAMAGING PELLICLE	4/19/2002	12/31/2002
6,790,292	10/262,443	US	Issued	RETICLE CLEANING WITHOUT DAMAGING PELLICLE	9/30/2002	9/14/2004
6,713,218	10/328,771	US	Issued	RETICLE CLEANING WITHOUT DAMAGING PELLICLE	12/23/2002	3/30/2004
6,424,733	09/118,835	US	Issued	METHOD AND APPARATUS FOR INSPECTING WAFERS	7/20/1998	7/23/2002
6,355,536	09/093,217	US	Issued	SELECTIVE METHOD TO FORM ROUGHENED SILICON	6/8/1998	3/12/2002
6,607,966	10/039,022	US	Issued	SELECTIVE METHOD TO FORM ROUGHENED SILICON	1/2/2002	8/19/2003

6,007,406	08/984,730	US	Issued	POLISHING SYSTEMS, METHODS OF POLISHING SUBSTRATES, AND METHODS OF PREPARING LIQUIDS FOR SEMICONDUCTOR FABRICATION PROCESSES	12/4/1997	12/28/1999
6,716,802	09/298,160	US	Issued	POLISHING SYSTEMS, METHODS OF POLISHING SUBSTRATES, AND METHODS OF PREPARING LIQUIDS FOR SEMICONDUCTOR FABRICATION PROCESSES	4/22/1999	4/6/2004
6,206,757	09/298,012	US	Issued	POLISHING SYSTEMS, METHODS OF POLISHING SUBSTRATES, AND METHODS OF PREPARING LIQUIDS FOR SEMICONDUCTOR FABRICATION PROCESSES	4/22/1999	3/27/2001
6,200,196	09/298,312	US	Issued	POLISHING SYSTEMS, METHODS OF POLISHING SUBSTRATES, AND METHODS OF PREPARING LIQUIDS FOR SEMICONDUCTOR FABRICATION PROCESSES	4/22/1999	3/13/2001
6,719,823	10/271,522	US	Issued	POLISHING SYSTEMS, METHODS OF POLISHING SUBSTRATES, AND METHODS OF PREPARING LIQUIDS FOR SEMICONDUCTOR FABRICATION PROCESSES	10/15/2002	4/13/2004
6,111,285	09/042,791	US	Issued	BORIDE ELECTRODES AND BARRIERS FOR CELL DIELECTRICS	3/17/1998	8/29/2000
6,316,800	09/563,909	US	Issued	BORIDE ELECTRODES AND BARRIERS FOR CELL DIELECTRICS	5/4/2000	11/13/2001
6,518,121	09/941,759	US	Issued	BORIDE ELECTRODES AND BARRIERS FOR CELL DIELECTRICS	8/30/2001	2/11/2003
6,316,356	09/038,252	US	Issued	THERMAL PROCESSING OF METAL ALLOYS FOR AN IMPROVED CMP PROCESS IN INTEGRATED CIRCUIT FABRICATION	3/10/1998	11/13/2001
6,774,035	09/942,201	US	Issued	THERMAL PROCESSING OF METAL ALLOYS FOR AN IMPROVED CMP PROCESS IN INTEGRATED CIRCUIT FABRICATION	8/29/2001	8/10/2004

6,784,550	09/945,536	US	Issued	THERMAL PROCESSING OF METAL ALLOYS FOR AN IMPROVED CMP PROCESS IN INTEGRATED CIRCUIT FABRICATION	8/30/2001	8/31/2004
	2000-569428	JP	Pending	DIFFUSION BARRIER LAYERS AND METHODS OF FORMING SAME	3/5/2001	
441,190	2001-7002560	KR	Issued	DIFFUSION BARRIER LAYERS AND METHODS OF FORMING SAME	2/27/2001	7/12/2004
WO 0014778	PCT/US99/20053	WO	Abandoned	DIFFUSION BARRIER LAYERS AND METHODS OF FORMING SAME	8/31/1999	
6,323,081	09/146,866	US	Issued	DIFFUSION BARRIER LAYERS AND METHODS OF FORMING SAME	9/3/1998	11/27/2001
	09/942,200	US	Abandoned	DIFFUSION BARRIER LAYERS AND METHODS OF FORMING SAME	8/29/2001	
6,265,781	09/153,053	US	Issued	METHODS AND SOLUTIONS FOR CLEANING POLISHED ALUMINUM-CONTAINING LAYERS, METHODS FOR MAKING METALLIZATION STRUCTURES, AND THE STRUCTURES RESULTING FROM THESE METHODS	9/15/1998	7/24/2001
6,635,562	09/841,973	US	Issued	METHODS AND SOLUTIONS FOR CLEANING POLISHED ALUMINUM-CONTAINING LAYERS, METHODS FOR MAKING METALLIZATION STRUCTURES, AND THE STRUCTURES RESULTING FROM THESE METHODS	4/25/2001	10/21/2003
	10/157,480	US	Abandoned	SOLUTIONS FOR CLEANING POLISHED ALUMINUM-CONTAINING LAYERS	5/29/2002	
6,369,432	09/028,050	US	Issued	ENHANCED CAPACITOR SHAPE	2/23/1998	4/9/2002
6,391,709	09/394,401	US	Issued	ENHANCED CAPACITOR SHAPE	9/13/1999	5/21/2002
6,418,008	09/798,992	US	Issued	ENHANCED CAPACITOR SHAPE	3/6/2001	7/9/2002
6,339,026	09/066,614	US	Issued	SEMICONDUCTOR PROCESSING METHODS OF POLISHING ALUMINUM-COMPRISING LAYERS	4/24/1998	1/15/2002

6,278,188	09/107,929	US	Issued	SEMICONDUCTOR CONSTRUCTIONS COMPRISING ALUMINUM-CONTAINING LAYERS	6/30/1998	8/21/2001
6,522,010	09/902,279	US	Issued	SEMICONDUCTOR CONSTRUCTIONS COMPRISING ALUMINUM-CONTAINING LAYERS	7/9/2001	2/18/2003
6,281,543	09/386,833	US	Issued	DOUBLE LAYER ELECTRODE AND BARRIER SYSTEMS ON HSG FOR HIGH K DIELECTRICS	8/31/1999	8/28/2001
6,399,459	09/892,594	US	Issued	DOUBLE LAYER ELECTRODE AND BARRIER SYSTEM ON HEMISPHERICAL GRAIN SILICON FOR USE WITH HIGH DIELECTRIC CONSTANT MATERIALS AND METHODS FOR FABRICATING THE SAME	6/27/2001	6/4/2002
6,673,689	10/159,892	US	Issued	DOUBLE LAYER ELECTRODE AND BARRIER SYSTEM ON HEMISPHERICAL GRAIN SILICON FOR USE WITH HIGH DIELECTRIC CONSTANT MATERIALS AND METHODS FOR FABRICATING THE SAME	5/30/2002	1/6/2004
6,018,175	09/148,032	US	Issued	GAPPED-PLATE CAPACITOR	9/3/1998	1/25/2000
6,316,326	09/229,857	US	Issued	GAPPED-PLATE CAPACITOR	1/13/1999	11/13/2001
6,498,363	09/652,837	US	Issued	GAPPED-PLATE CAPACITOR	8/31/2000	12/24/2002
6,774,421	10/286,715	US	Issued	GAPPED-PLATE CAPACITOR	11/1/2002	8/10/2004
6,958,901	10/853,851	US	Issued	GAPPED-PLATE CAPACITOR	5/25/2004	10/25/2005
7,151,659	11/038,602	US	Issued	GAPPED-PLATE CAPACITOR	1/18/2005	12/19/2006
	11/599,204	US	Abandoned	GAPPED-PLATE CAPACITOR	11/14/2006	
ZL01810919.5	1810919.5	CN	Issued	METHODS FOR FORMING AND INTEGRATED CIRCUIT STRUCTURES CONTAINING RUTHENIUM AND TUNGSTEN CONTAINING LAYERS	6/7/2001	8/16/2006
	1942105.6	EP	Pending	METHODS FOR FORMING AND INTEGRATED CIRCUIT STRUCTURES CONTAINING RUTHENIUM AND TUNGSTEN CONTAINING LAYERS	6/7/2001	
4,216,585	502821/2002	JP	Issued	METHODS FOR FORMING AND INTEGRATED CIRCUIT STRUCTURES CONTAINING RUTHENIUM AND TUNGSTEN CONTAINING LAYERS	6/7/2001	11/14/2008

746,192	10-2002-7016728	KR	Issued	METHODS FOR FORMING AND INTEGRATED CIRCUIT STRUCTURES CONTAINING RUTHENIUM AND TUNGSTEN CONTAINING LAYERS	12/7/2002	7/30/2007
wo 01/95378	pct/us01/18585	WO	Abandoned	METHODS FOR FORMING AND INTEGRATED CIRCUIT STRUCTURES CONTAINING RUTHENIUM AND TUNGSTEN CONTAINING LAYERS	6/7/2001	
7,253,076	09/590,795	US	Issued	METHODS FOR FORMING AND INTEGRATED CIRCUIT STRUCTURES CONTAINING RUTHENIUM AND TUNGSTEN CONTAINING LAYERS	6/8/2000	8/7/2007
ZL200610092516.9	2006-10092516.9	CN	Issued	METHODS FOR FORMING AND INTEGRATED CIRCUIT STRUCTURES CONTAINING RUTHENIUM AND TUNGSTEN CONTAINING LAYERS	6/7/2001	12/24/2008
6,833,576	10/002,779	US	Issued	METHODS FOR FORMING AND INTEGRATED CIRCUIT STRUCTURES CONTAINING RUTHENIUM AND TUNGSTEN CONTAINING LAYERS	10/29/2001	12/21/2004
6,596,583	10/002,906	US	Issued	METHODS FOR FORMING AND INTEGRATED CIRCUIT STRUCTURES CONTAINING RUTHENIUM AND TUNGSTEN CONTAINING LAYERS	10/29/2001	7/22/2003
	10/226,008	US	Abandoned	METHODS FOR FORMING AND INTEGRATED CIRCUIT STRUCTURES CONTAINING RUTHENIUM AND TUNGSTEN CONTAINING LAYERS	8/21/2002	
	11/235,866	US	Abandoned	METHODS FOR FORMING AND INTEGRATED CIRCUIT STRUCTURES CONTAINING RUTHENIUM AND TUNGSTEN CONTAINING LAYERS	9/26/2005	
6,223,331	09/126,877	US	Issued	SEMICONDUCTOR CIRCUIT DESIGN METHODS, SEMICONDUCTOR PROCESSING METHODS AND INTEGRATED CIRCUITRY	7/30/1998	4/24/2001
6,434,732	09/823,104	US	Issued	SEMICONDUCTOR AND CIRCUIT DESIGN METHODS EMPLOYING SPACING CONSTRAINTS	3/29/2001	8/13/2002
6,509,590	09/119,355	US	Issued	ALUMINUM BERYLLIUM ALLOYS FOR AIR BRIDGES	7/20/1998	1/21/2003

6,717,191	10/349,015	US	Issued	ALUMINUM BERYLLIUM ALLOYS FOR AIR BRIDGES	1/21/2003	4/6/2004
6,943,090	10/819,025	US	Issued	ALUMINUM BERYLLIUM ALLOYS FOR AIR BRIDGES	4/6/2004	9/13/2005
6,316,363	09/387,429	US	Issued	DEADHESION METHOD AND MECHANISM FOR WAFER PROCESSING	9/2/1999	11/13/2001
6,506,679	09/942,181	US	Issued	DEADHESION METHOD AND MECHANISM FOR WAFER PROCESSING	8/29/2001	1/14/2003
6,693,034	10/229,868	US	Issued	DEADHESION METHOD AND MECHANISM FOR WAFER PROCESSING	8/27/2002	2/17/2004
6,395,647	09/388,570	US	Issued	CHEMICAL TREATMENT OF SEMICONDUCTOR SUBSTRATES	9/2/1999	5/28/2002
6,774,058	10/027,519	US	Issued	CHEMICAL TREATMENT OF SEMICONDUCTOR SUBSTRATES	12/20/2001	8/10/2004
7,008,885	10/913,555	US	Issued	CHEMICAL TREATMENT OF SEMICONDUCTOR SUBSTRATES	8/6/2004	3/7/2006
7,314,837	11/333,629	US	Issued	CHEMICAL TREATMENT OF SEMICONDUCTOR SUBSTRATES	12/29/2005	1/1/2008
6,750,500	09/225,887	US	Issued	CAPACITOR ELECTRODE FOR INTEGRATING HIGH K MATERIALS	1/5/1999	6/15/2004
6,580,115	09/880,536	US	Issued	CAPACITOR ELECTRODE FOR INTEGRATING HIGH K MATERIALS	7/19/2001	6/17/2003
	10/868,173	US	Abandoned	CAPACITOR ELECTRODE FOR INTEGRATING HIGH K MATERIALS	6/14/2004	
6,387,748	09/251,104	US	Issued	METHOD OF FORMING SEMICONDUCTOR CIRCUIT CONSTRUCTIONS AND CAPACITOR CONSTRUCTIONS	2/16/1999	5/14/2002
6,555,863	09/566,673	US	Issued	SEMICONDUCTOR CIRCUIT CONSTRUCTIONS, CAPACITOR CONSTRUCTIONS, AND METHODS OF FORMING SEMICONDUCTOR CIRCUIT CONSTRUCTIONS AND CAPACITOR CONSTRUCTIONS	5/8/2000	4/29/2003

6,638,809	09/894,320	US	Issued	METHODS OF FORMING SEMICONDUCTOR CIRCUIT CONSTRUCTIONS AND CAPACITOR CONSTRUCTIONS	6/27/2001	10/28/2003
6,780,792	10/423,423	US	Issued	SEMICONDUCTOR CIRCUIT CONSTRUCTIONS, CAPACITOR CONSTRUCTIONS, AND METHODS OF FORMING SEMICONDUCTOR CIRCUIT CONSTRUCTIONS AND CAPACITOR CONSTRUCTIONS	4/25/2003	8/24/2004
6,342,417	09/250,974	US	Issued	METHODS OF FORMING MATERIALS COMPRISING TUNGSTEN AND NITROGEN	2/16/1999	1/29/2002
6,395,614	09/751,075	US	Issued	METHODS OF FORMING MATERIALS COMPRISING TUNGSTEN AND NITROGEN, AND METHODS OF FORMING CAPACITORS	12/29/2000	5/28/2002
		US	Abandoned	METHODS OF FORMING MATERIALS COMPRISING TUNGSTEN AND NITROGEN, AND METHODS OF FORMING CAPACITORS	2/13/2002	
6,682,972	10/035,390	US	Issued	METHODS OF FORMING MATERIALS COMPRISING TUNGSTEN AND NITROGEN	12/28/2001	1/27/2004
	10/755,001	US	Abandoned	METHODS OF FORMING MATERIALS COMPRISING TUNGSTEN AND NITROGEN, AND METHODS OF FORMING CAPACITORS	1/9/2004	
	11/452,816	US	Abandoned	METHODS OF FORMING MATERIALS COMPRISING TUNGSTEN AND NITROGEN, AND METHODS OF FORMING CAPACITORS	6/13/2006	
6,468,909	09/146,299	US	Issued	ISOLATION AND/OR REMOVAL OF IONIC CONTAMINANTS FROM PLANARIZATION FLUID COMPOSITIONS USING MACROCYCLIC POLYETHERS AND METHODS OF USING SUCH COMPOSITIONS	9/3/1998	10/22/2002
6,458,290	09/642,682	US	Issued	ISOLATION AND/OR REMOVAL OF IONIC CONTAMINANTS FROM PLANARIZATION FLUID COMPOSITIONS USING MACROCYCLIC	8/21/2000	10/1/2002

				POLYETHERS				
6,025,624	09/099,765	US	Issued	SHARED LENGTH CELL FOR IMPROVED CAPACITANCE	6/19/1998	2/15/2000		
6,180,452	09/436,213	US	Issued	SHARED LENGTH CELL FOR IMPROVED CAPACITANCE	11/9/1999	1/30/2001		
6,373,084	09/729,848	US	Issued	SHARED LENGTH CELL FOR IMPROVED CAPACITANCE	12/6/2000	4/16/2002		
6,750,110	09/121,528	US	Issued	CONTINUOUS GOOD STEP COVERAGE CVD PLATINUM METAL DEPOSITION	7/23/1998	6/15/2004		
6,861,693	09/373,355	US	Issued	CONTINUOUS GOOD STEP COVERAGE CVD PLATINUM METAL DEPOSITION	8/12/1999	3/1/2005		
		US	Abandoned	CONTINUOUS GOOD STEP COVERAGE CVD PLATINUM METAL DEPOSITION	7/12/2004			
6,451,714	09/139,934	US	Issued	SYSTEM AND METHOD FOR SELECTIVELY INCREASING SURFACE TEMPERATURE OF AN OBJECT	8/26/1998	9/17/2002		
	10/238,141	US	Abandoned	SYSTEM AND METHOD FOR SELECTIVELY INCREASING SURFACE TEMPERATURE OF AN OBJECT	9/10/2002			
	10/931,406	US	Abandoned	SYSTEM AND METHOD FOR SELECTIVELY INCREASING SURFACE TEMPERATURE OF AN OBJECT	8/31/2004			
7,247,584	10/931,592	US	Issued	SYSTEM AND METHOD FOR SELECTIVELY INCREASING SURFACE TEMPERATURE OF AN OBJECT	8/31/2004	7/24/2007		
6,265,722	09/386,976	US	Issued	ORGANIC FIELD IONIZATION SOURCE	8/31/1999	7/24/2001		
6,429,439	09/891,919	US	Issued	ORGANIC FIELD IONIZATION SOURCE	6/26/2001	8/6/2002		
6,426,295	09/584,468	US	Issued	REDUCTION OF SURFACE ROUGHNESS DURING CHEMICAL MECHANICAL PLANARIZATION (CMP)	5/31/2000	7/30/2002		

6,630,403	10/209,035	US	Issued	REDUCTION OF SURFACE ROUGHNESS DURING CHEMICAL MECHANICAL PLANARIZATION (CMP)	7/30/2002	10/7/2003
6,403,442	09/389,533	US	Issued	METHODS OF FORMING CAPACITORS AND RESULTANT CAPACITOR STRUCTURES	9/2/1999	6/11/2002
6,459,138	09/880,579	US	Issued	CAPACITOR STRUCTURES	6/12/2001	10/1/2002
6,492,243	09/990,715	US	Issued	METHODS OF FORMING CAPACITORS AND RESULTANT CAPACITOR STRUCTURES	11/20/2001	12/10/2002
6,844,230	10/082,594	US	Issued	METHODS OF FORMING CAPACITORS AND RESULTANT CAPACITOR STRUCTURES	2/22/2002	1/18/2005
6,806,197	09/924,816	US	Issued	METHOD OF FORMING INTEGRATED CIRCUITRY, AND METHOD FOR FORMING A CONTACT OPENING	8/7/2001	10/19/2004
7,291,895	10/391,952	US	Issued	INTEGRATED CIRCUITRY	3/18/2003	11/6/2007
	11/254,680	US	Abandoned	INTEGRATED CIRCUITRY	10/19/2005	
6,319,832	09/253,307	US	Issued	METHODS OF MAKING SEMICONDUCTOR DEVICES (AS AMENDED)	2/19/1999	11/20/2001
6,656,839	09/880,580	US	Issued	SOLUTIONS OF METAL-COMPRISE MATERIALS, AND METHODS OF MAKING SOLUTIONS OF METAL-COMPRISE MATERIALS	6/12/2001	12/2/2003
6,495,459	09/999,840	US	Issued	SOLUTIONS OF METAL-COMPRISE MATERIALS, METHODS OF FORMING METAL-COMPRISE LAYERS, METHODS OF STORING METAL- COMPRISE MATERIALS, AND METHODS OF FORMING CAPACITORS	10/24/2001	12/17/2002
6,773,495	10/336,087	US	Issued	SOLUTIONS OF METAL-COMPRISE MATERIALS	1/3/2003	8/10/2004
6,204,143	09/293,635	US	Issued	A METHOD OF FORMING HIGH ASPECT RATIO STRUCTURES FOR SEMICONDUCTOR DEVICES	4/15/1999	3/20/2001
	09/765,122	US	Abandoned	A METHOD OF FORMING HIGH ASPECT RATIO STRUCTURES FOR SEMICONDUCTOR DEVICES	1/17/2001	
6,319,789	09/235,752	US	Issued	METHOD FOR IMPROVED PROCESSING AND ETCHBACK OF A CONTAINER CAPACITOR	1/25/1999	11/20/2001

6,693,015	09/928,308	US	Issued	METHOD FOR IMPROVED PROCESSING AND ETCHBACK OF A CONTAINER CAPACITOR	8/14/2001	2/17/2004
6,809,918	10/735,897	US	Issued	METHOD FOR IMPROVED PROCESSING AND ETCHBACK OF A CONTAINER CAPACITOR	12/16/2003	10/26/2004
6,365,507	09/260,237	US	Issued	METHOD OF FORMING INTEGRATED CIRCUITRY	3/1/1999	4/2/2002
6,518,626	09/507,463	US	Issued	METHOD OF FORMING LOW DIELECTRIC SILICON OXYNITRIDES SPACER FILMS HIGHLY SELECTIVE TO ETCHANTS	2/22/2000	2/11/2003
6,624,088	10/118,946	US	Issued	METHOD OF FORMING LOW DIELECTRIC SILICON OXYNITRIDES SPACER FILMS HIGHLY SELECTIVE TO ETCHANTS	4/10/2002	9/23/2003
6,774,418	10/303,779	US	Issued	LOW DIELECTRIC SILICON OXYNITRIDE SPACER FILMS AND DEVICES INCORPORATING SUCH FILMS	11/25/2002	8/10/2004
6,300,187	09/198,826	US	Issued	METHOD OF FORMING A CAPACITOR	11/24/1998	10/9/2001
6,313,496	09/654,930	US	Issued	METHOD OF FORMING A CAPACITOR	8/31/2000	11/6/2001
7,009,240	09/598,355	US	Issued	STRUCTURES AND METHODS FOR ENHANCING CAPACITORS IN INTEGRATED CIRCUITS	6/21/2000	3/7/2006
7,232,721	10/931,396	US	Issued	STRUCTURES AND METHODS FOR ENHANCING CAPACITORS IN INTEGRATED CIRCUITS	8/31/2004	6/19/2007
	11/343,440	US	Abandoned	STRUCTURES AND METHODS FOR ENHANCING CAPACITORS IN INTEGRATED CIRCUITS	1/31/2006	
7,390,712	11/796,773	US	Issued	STRUCTURES AND METHODS FOR ENHANCING CAPACITORS IN INTEGRATED CIRCUITS	4/30/2007	6/24/2008
6,624,897	09/292,396	US	Issued	APPARATUS AND METHOD FOR FEATURE EDGE DETECTION IN SEMICONDUCTOR PROCESSING	4/15/1999	9/23/2003
6,573,993	10/206,042	US	Issued	APPARATUS AND METHOD FOR FEATURE EDGE DETECTION IN SEMICONDUCTOR PROCESSING	7/29/2002	6/3/2003
7,006,227	10/417,191	US	Issued	AN APPARATUS FOR THE IN SITU ALIGNMENT OF A MASK AND A SEMICONDUCTOR WAFER	4/17/2003	2/28/2006

		US	Abandoned	APPARATUS AND METHOD FOR FEATURE EDGE DETECTION IN SEMICONDUCTOR PROCESSING	12/21/2005	
6,518,117	09/823,200	US	Issued	METHODS OF FORMING NITROGEN-CONTAINING MASSES, SILICON NITRIDE LAYERS, AND CAPACITOR CONSTRUCTIONS	3/29/2001	2/11/2003
6,967,134	10/339,695	US	Issued	METHODS OF FORMING NITROGEN-CONTAINING MASSES, SILICON NITRIDE LAYERS, AND CAPACITOR CONSTRUCTIONS	1/8/2003	11/22/2005
7,012,294	11/203,046	US	Issued	SEMICONDUCTOR CONSTRUCTIONS	8/12/2005	3/14/2006
7,244,648	11/375,696	US	Issued	METHODS OF FORMING SEMICONDUCTOR CONSTRUCTIONS	3/13/2006	7/17/2007
6,277,687	09/323,440	US	Issued	METHOD OF FORMING A PAIR OF CAPACITORS HAVING A COMMON CAPACITOR ELECTRODE, METHOD OF FORMING DRAM CIRCUITRY, INTEGRATED CIRCUITRY AND DRAM CIRCUITRY	6/1/1999	8/21/2001
6,570,204	09/654,297	US	Issued	INTEGRATED CIRCUITRY AND DRAM CIRCUITRY	9/1/2000	5/27/2003
6,716,077	09/572,079	US	Issued	A METHOD OF FORMING FLOW FILL STRUCTURES	5/17/2000	4/6/2004
7,116,042	10/314,228	US	Issued	FLOW FILL STRUCTURES	12/9/2002	10/3/2006
6,966,810	10/658,468	US	Issued	METHOD OF FORMING FLOW FILL STRUCTURES	9/10/2003	11/22/2005
	11/507,027	US	Abandoned	FLOW FILL STRUCTURES	8/21/2006	
	PCT/US00/22289	WO	Abandoned	DELIVERY OF DISSOLVED OZONE	8/14/2000	
6,758,938	09/386,247	US	Issued	DELIVERY OF DISSOLVED OZONE	8/31/1999	7/6/2004
6,645,874	09/864,482	US	Issued	DELIVERY OF DISSOLVED OZONE	5/24/2001	11/11/2003
	10/847,222	US	Abandoned	DELIVERY OF DISSOLVED OZONE	5/17/2004	
	10/829,638	US	Abandoned	DELIVERY OF DISSOLVED OZONE	6/3/2004	
6,682,969	09/652,863	US	Issued	TOP ELECTRODE IN A STRONGLY OXIDIZING ENVIRONMENT	8/31/2000	1/27/2004
7,023,043	10/039,215	US	Issued	TOP ELECTRODE IN A STRONGLY OXIDIZING ENVIRONMENT	1/3/2002	4/4/2006

	11/398,498	US	Abandoned	TOP ELECTRODE IN A STRONGLY OXIDIZING ENVIRONMENT	4/4/2006	
6,524,346	09/259,143	US	Issued	STEREOLITHOGRAPHIC METHOD FOR APPLYING MATERIALS TO ELECTRONIC COMPONENT SUBSTRATES AND RESULTING STRUCTURES	2/26/1999	2/25/2003
	10/338,602	US	Abandoned	ELECTRONIC COMPONENT SUBSTRATES AND ASSOCIATED STRUCTURES	1/8/2003	
6,440,382	09/387,119	US	Issued	METHOD FOR PRODUCING WATER FOR USE IN MANUFACTURING SEMICONDUCTORS	8/31/1999	8/27/2002
7,033,554	10/123,441	US	Issued	METHOD FOR PRODUCING WATER FOR USE IN MANUFACTURING SEMICONDUCTORS	4/15/2002	4/25/2006
6,787,479	10/125,762	US	Issued	METHOD FOR PRODUCING WATER FOR USE IN MANUFACTURING SEMICONDUCTORS	4/18/2002	9/7/2004
7,071,120	10/392,114	US	Issued	METHOD FOR PRODUCING WATER FOR USE IN MANUFACTURING SEMICONDUCTORS	3/18/2003	7/4/2006
	11/438,676	US	Abandoned	METHOD FOR PRODUCING WATER FOR USE IN MANUFACTURING SEMICONDUCTORS	5/22/2006	
	09/379,092	US	Abandoned	FORMING SIDEWALL OXIDE LAYERS FOR TRENCH ISOLATION	8/23/1999	
6,548,372	09/685,531	US	Issued	FORMING SIDEWALL OXIDE LAYERS FOR TRENCH ISOLATION	10/10/2000	4/15/2003
7,275,925	09/944,488	US	Issued	APPARATUS FOR STEREOLITHOGRAPHIC PROCESSING OF COMPONENTS AND ASSEMBLIES	8/30/2001	10/2/2007
6,911,173	10/455,091	US	Issued	METHODS AND APPARATUS FOR STEREOLITHOGRAPHIC PROCESSING OF COMPONENTS AND ASSEMBLIES	6/5/2003	6/28/2005
	10/672,098	US	Abandoned	APPARATUS AND METHODS FOR USE IN STEREOLITHOGRAPHIC PROCESSING OF COMPONENTS AND ASSEMBLIES	9/26/2003	

	11/702,473	US	Abandoned	APPARATUS FOR USE IN STEREO LITHOGRAPHIC PROCESSING OF COMPONENTS AND ASSEMBLIES	2/5/2007	
6,573,175	09/998,729	US	Issued	DRY LOW K FILM APPLICATION FOR INTERLEVEL DIELECTRIC AND METHOD OF CLEANING ETCHED FEATURES	11/30/2001	6/3/2003
6,605,863	10/178,398	US	Issued	LOW K FILM APPLICATION FOR INTERLEVEL DIELECTRIC AND METHOD OF CLEANING ETCHED FEATURES	6/24/2002	8/12/2003
6,890,865	10/423,210	US	Issued	LOW K FILM APPLICATION FOR INTERLEVEL DIELECTRIC AND METHOD OF CLEANING ETCHED FEATURES	4/25/2003	5/10/2005
	10/462,467	US	Abandoned	LOW K FILM APPLICATION FOR INTERLEVEL DIELECTRIC AND METHOD OF CLEANING ETCHED FEATURES	6/16/2003	
	10/870,216	US	Abandoned	LOW K FILM APPLICATION FOR INTERLEVEL DIELECTRIC AND METHOD OF CLEANING ETCHED FEATURES	6/17/2004	
6,342,445	09/571,718	US	Issued	METHOD OF FABRICATING AN SRRUO3 FILM	5/15/2000	1/29/2002
6,506,666	10/003,261	US	Issued	METHOD OF FABRICATING AN SRRUO3 FILM	12/6/2001	1/14/2003
6,813,136	10/303,017	US	Issued	METHOD OF FABRICATING AN SRRUO3 FILM	11/25/2002	11/2/2004
ZL02804918.7	2804918.7	CN	Issued	RHODIUM-RICH OXYGEN BARRIERS	2/11/2002	3/5/2008
1,368,822	2742467	DK	Issued	RHODIUM-RICH OXYGEN BARRIERS	8/28/2003	11/22/2006
1,368,822	2742467	EP	Issued	RHODIUM-RICH OXYGEN BARRIERS	8/28/2003	11/22/2006
1,368,822	2742467	FR	Issued	RHODIUM-RICH OXYGEN BARRIERS	8/28/2003	11/22/2006
1,368,822	2742467	GB	Issued	RHODIUM-RICH OXYGEN BARRIERS	8/23/2003	11/22/2006
1,368,822	2742467	IT	Issued	RHODIUM-RICH OXYGEN BARRIERS	8/28/2003	11/22/2006
	2002-566534	JP	Pending	RHODIUM-RICH OXYGEN BARRIERS	2/11/2002	
10-0510303	7010896/2003	KR	Issued	RHODIUM-RICH OXYGEN BARRIERS	2/11/2002	8/1/2006
	pct/us02/04090	WO	Completed	RHODIUM-RICH OXYGEN BARRIERS	2/11/2002	
99,038	200305148-9	SG	Issued	RHODIUM-RICH OXYGEN BARRIERS	2/11/2002	10/31/2005

6,518,610	09/789,335	US	Issued	RHODIUM-RICH OXYGEN BARRIERS	2/20/2001	2/11/2003
6,740,554	10/209,386	US	Issued	METHODS TO FORM RHODIUM-RICH OXYGEN BARRIERS	7/30/2002	5/25/2004
6,781,175	10/318,597	US	Issued	RHODIUM-RICH INTEGRATED CIRCUIT CAPACITOR ELECTRODE	12/12/2002	8/24/2004
7,038,263	10/850,664	US	Issued	INTEGRATED CIRCUITS WITH RHODIUM-RICH STRUCTURE	5/21/2004	5/2/2006
6,541,067	09/506,962	US	Issued	SOLVATED RUTHENIUM PRECURSORS FOR DIRECT LIQUID INJECTION OF RUTHENIUM AND RUTHENIUM OXIDE AND METHOD OF USING SAME	2/18/2000	4/1/2003
6,517,616	10/012,668	US	Issued	SOLVATED RUTHENIUM PRECURSORS FOR DIRECT LIQUID INJECTION OF RUTHENIUM AND RUTHENIUM OXIDE	10/30/2001	2/11/2003
6,844,261	10/322,264	US	Issued	METHOD OF FORMING RUTHENIUM AND RUTHENIUM OXIDE FILMS ON A SEMICONDUCTOR SUBSTRATE	12/17/2002	1/18/2005
6,840,988	10/365,204	US	Issued	SOLVATED RUTHENIUM PRECURSORS FOR DIRECT LIQUID INJECTION OF RUTHENIUM AND RUTHENIUM OXIDE	2/11/2003	1/11/2005
6,458,714	09/721,839	US	Issued	METHOD OF SELECTIVE OXIDATION IN SEMICONDUCTOR MANUFACTURE	11/22/2000	10/1/2002
6,524,867	09/751,810	US	Issued	METHOD FOR FORMING PLATINUM-RHODIUM STACK AS AN OXYGEN BARRIER	12/28/2000	2/25/2003
6,759,705	10/268,482	US	Issued	PLATINUM-RHODIUM STACK AS AN OXYGEN BARRIER IN AN INTEGRATED CIRCUIT CAPACITOR	10/10/2002	7/6/2004
6,858,536	10/313,088	US	Issued	PROCESSES TO FORM A METALLIC FILM STACK	12/5/2002	2/22/2005
6,916,380	10/871,965	US	Issued	SYSTEM FOR DEPOSITING A LAYERED FILM	6/18/2004	7/12/2005
	11/138,809	US	Abandoned	SYSTEM FOR DEPOSITING A LAYERED FILM	5/26/2005	

6,861,007	09/798,806	US	Issued	METHOD FOR REMOVING ORGANIC MATERIAL FROM A SUBSTRATE AND FOR OXIDIZING OXIDIZABLE MATERIAL THEREON	3/2/2001	3/1/2005
7,056,447	10/672,816	US	Issued	SEMICONDUCTOR PROCESSING METHODS	9/26/2003	6/6/2006
6,630,706	09/945,252	US	Issued	LOCALIZED ARRAY THRESHOLD VOLTAGE IMPLANT TO ENHANCE CHARGE STORAGE WITHIN DRAM MEMORY CELLS	8/30/2001	10/7/2003
6,800,520	10/234,576	US	Issued	LOCALIZED ARRAY THRESHOLD VOLTAGE IMPLANT TO ENHANCE CHARGE STORAGE WITHIN DRAM MEMORY CELLS	8/30/2002	10/5/2004
6,815,287	10/437,494	US	Issued	LOCALIZED ARRAY THRESHOLD VOLTAGE IMPLANT TO ENHANCE CHARGE STORAGE WITHIN DRAM MEMORY CELLS	5/14/2003	11/9/2004
	10/983,971	US	Abandoned	LOCALIZED ARRAY THRESHOLD VOLTAGE IMPLANT TO ENHANCE CHARGE STORAGE WITHIN DRAM MEMORY CELLS	11/8/2004	
451995	2807854.3	CN	Issued	DYNAMIC MEMORY BASED ON SINGLE ELECTRON STORAGE	2/1/2002	12/17/2008
	1358669	EP	Pending	DYNAMIC MEMORY BASED ON SINGLE ELECTRON STORAGE	2/1/2002	
10-0862414	2003-7010439	KR	Issued	DYNAMIC MEMORY BASED ON SINGLE ELECTRON STORAGE	8/7/2003	10/1/2008
	pct/us02/02761	WO	Abandoned	DYNAMIC MEMORY BASED ON SINGLE ELECTRON STORAGE	2/1/2002	
6,683,337	09/779,547	US	Issued	DYNAMIC MEMORY BASED ON SINGLE ELECTRON STORAGE	2/9/2001	1/27/2004
6,730,567	10/093,528	US	Issued	DYNAMIC MEMORY BASED ON SINGLE ELECTRON STORAGE	3/11/2002	5/4/2004
6,479,297	09/652,634	US	Issued	DETECTION DEVICES, METHODS AND SYSTEMS FOR DETECTING GAS PHASE MATERIALS	8/31/2000	11/12/2002

6,689,321	10/266,797	US	Issued	DETECTION DEVICES, METHODS AND SYSTEMS FOR GAS PHASE MATERIALS	10/8/2002	2/10/2004
6,927,067	10/771,043	US	Issued	DETECTION DEVICES, METHODS AND SYSTEMS FOR GAS PHASE MATERIALS	2/3/2004	8/9/2005
	11/172,584	US	Abandoned	DETECTION DEVICES, METHODS AND SYSTEMS FOR GAS PHASE MATERIALS	6/30/2005	
6,383,868	09/653,501	US	Issued	METHODS FOR FORMING CONTACT AND CONTAINER STRUCTURES, AND INTEGRATED CIRCUIT DEVICES THEREFROM	8/31/2000	5/7/2002
6,617,635	10/039,950	US	Issued	INTEGRATED CIRCUIT DEVICES HAVING CONTACT AND CONTAINER STRUCTURES	12/31/2001	9/9/2003
6,730,444	09/874,615	US	Issued	NEEDLE COMB RETICLE PATTERN FOR CRITICAL DIMENSION AND REGISTRATION MEASUREMENTS USING A REGISTRATION TOOL AND METHODS FOR USING SAME	6/5/2001	5/4/2004
6,908,639	09/825,087	US	Issued	MIXED COMPOSITION INTERFACE LAYER AND METHOD OF FORMING	4/2/2001	6/21/2005
7,273,660	10/228,404	US	Issued	MIXED COMPOSITION INTERFACE LAYER AND METHOD OF FORMING	8/26/2002	9/25/2007
6,429,070	09/651,484	US	Issued	DRAM CELL CONSTRUCTIONS, AND METHODS OF FORMING DRAM CELLS	8/30/2000	8/6/2002
6,639,243	10/012,233	US	Issued	DRAM CELL CONSTRUCTIONS	12/5/2001	10/28/2003
6,734,062	10/188,022	US	Issued	METHODS OF FORMING DRAM CELLS	7/1/2002	5/11/2004
6,707,090	10/393,696	US	Issued	DRAM CELL CONSTRUCTIONS	3/20/2003	3/16/2004
	60/310,938	US	Abandoned	DRAM DEVICES, AND METHODS OF FORMING DRAM DEVICES	8/7/2001	
6,645,806	09/941,375	US	Issued	METHODS OF FORMING DRAMS, METHODS OF FORMING ACCESS TRANSISTORS FOR DRAM DEVICES, AND METHODS OF FORMING TRANSISTOR SOURCE/DRAIN REGIONS	8/28/2001	11/11/2003

7,105,881	10/325,159	US	Issued	DRAM DEVICES, AND METHODS OF FORMING DRAM DEVICES	12/19/2002	9/12/2006
6,372,574	09/586,321	US	Issued	METHOD OF FORMING A CAPACITOR CONTAINER ELECTRODE AND METHOD OF PATTERNING A METAL LAYER BY ELECTIVELY SILICIZING THE ELECTRODE LAYER AND REMOVING THE SILICIZED PORTION	6/2/2000	4/16/2002
wo 02/058109		WO	Abandoned	REDUCED ASPECT RATIO DIGIT LINE CONTACT PROCESS FLOW USED DURING THE FORMATION OF A SEMICONDUCTOR DEVICE	1/14/2002	
6,709,945	09/765,885	US	Issued	REDUCED ASPECT RATIO DIGIT LINE CONTACT PROCESS FLOW USED DURING THE FORMATION OF A SEMICONDUCTOR DEVICE	1/16/2001	3/23/2004
7,015,528	10/807,952	US	Issued	REDUCED ASPECT RATIO DIGIT LINE CONTACT PROCESS FLOW USED DURING THE FORMATION OF A SEMICONDUCTOR DEVICE	3/23/2004	3/21/2006
6,552,383	09/852,668	US	Issued	INTEGRATED DECOUPLING CAPACITORS	5/11/2001	4/22/2003
6,812,109	10/372,813	US	Issued	INTEGRATED DECOUPLING CAPACITORS	2/26/2003	11/2/2004
6,461,909	09/651,859	US	Issued	PROCESS FOR FABRICATING RUSIXOY- CONTAINING ADHESION LAYERS	8/30/2000	10/8/2002
6,462,367	09/888,891	US	Issued	RUSIXOY-CONTAINING ADHESION LAYERS	6/25/2001	10/8/2002
6,610,568	09/935,490	US	Issued	PROCESS FOR FABRICATING RUSIXOY- CONTAINING ADHESION LAYERS	8/23/2001	8/26/2003
6,617,634	10/075,819	US	Issued	A CAPACITOR HAVING RUSIXOY-CONTAINING ADHESION LAYERS	2/12/2002	9/9/2003
6,800,937	10/075,863	US	Issued	RUSIXOY-CONTAINING ADHESION LAYERS	2/12/2002	10/5/2004
6,737,317	10/075,574	US	Issued	METHOD OF MANUFACTURING A CAPACITOR HAVING RUSIXOY-CONTAINING ADHESION LAYERS	2/12/2002	5/18/2004
6,764,895	10/158,978	US	Issued	PROCESS FOR FABRICATING RUSIXOY- CONTAINING ADHESION LAYERS	5/30/2002	7/20/2004

6,867,093	10/430,456	US	Issued	PROCESS FOR FABRICATING RUSIOX-CONTAINING ADHESION LAYERS	5/6/2003	3/15/2005
6,867,449	10/430,457	US	Issued	A CAPACITOR HAVING RUSIOX-CONTAINING ADHESION LAYERS	5/6/2003	3/15/2005
6,613,656	09/782,207	US	Issued	SEQUENTIAL PULSE DEPOSITION	2/13/2001	9/2/2003
	10/232,270	US	Abandoned	SEQUENTIAL PULSE DEPOSITION	8/28/2002	
	11/496,093	US	Pending	SEQUENTIAL PULSE DEPOSITION	7/31/2006	
6,696,360	09/809,670	US	Issued	BARRIER-METAL-FREE COPPER DAMASCENE TECHNOLOGY USING ATOMIC HYDROGEN ENHANCED REFLOW	3/15/2001	2/24/2004
6,762,500	10/122,870	US	Issued	BARRIER-METAL-FREE COPPER DAMASCENE TECHNOLOGY USING ATOMIC HYDROGEN ENHANCED REFLOW	4/15/2002	7/13/2004
7,186,643	10/889,203	US	Issued	BARRIER-METAL-FREE COPPER DAMASCENE TECHNOLOGY USING ATOMIC HYDROGEN ENHANCED REFLOW	7/12/2004	3/6/2007
	11/511,652	US	Pending	BARRIER-METAL-FREE COPPER DAMASCENE TECHNOLOGY USING ATOMIC HYDROGEN ENHANCED REFLOW	8/29/2006	
6,918,960	09/997,073	US	Issued	CVD OF PTRH WITH GOOD ADHESION AND MORPHOLOGY	11/28/2001	7/19/2005
	10/991,693	US	Abandoned	CVD OF PTRH WITH GOOD ADHESION AND MORPHOLOGY	11/18/2004	
6,794,100	09/945,316	US	Issued	METHOD FOR CONTROLLING RADIATION BEAM INTENSITY DIRECTED TO MICROLITHOGRAPHIC SUBSTRATE	8/30/2001	9/21/2004
7,046,340	10/870,561	US	Issued	METHOD FOR CONTROLLING RADIATION BEAM INTENSITY DIRECTED TO MICROLITHOGRAPHIC SUBSTRATE	6/16/2004	5/16/2006

7,230,679	11/397,176	US	Issued	METHOD FOR CONTROLLING RADIATION BEAM INTENSITY DIRECTED TO MICROLITHOGRAPHIC SUBSTRATE	4/4/2006	6/12/2007
6,515,325	10/092,829	US	Issued	NANOTUBE SEMICONDUCTOR DEVICES AND METHODS FOR MAKING THE SAME	3/6/2002	2/4/2003
6,858,891	10/315,511	US	Issued	NANOTUBE SEMICONDUCTOR DEVICES AND METHODS FOR MAKING THE SAME	12/9/2002	2/22/2005
7,081,385	10/822,113	US	Issued	NANOTUBE SEMICONDUCTOR DEVICES AND METHODS FOR MAKING THE SAME	4/8/2004	7/25/2006
6,803,155	09/917,697	US	Issued	MICROLITHOGRAPHIC DEVICE, MICROLITHOGRAPHIC ASSIST FEATURES SYSTEM FOR FORMING CONTACTS AND OTHER STRUCTURES AND METHOD OF DETERMINING MASK PATTERNS	7/31/2001	10/12/2004
7,008,738	10/847,337	US	Issued	MICROLITHOGRAPHIC STRUCTURES AND METHOD OF FABRICATION	5/18/2004	3/7/2006
	11/319,223	US	Abandoned	MICROLITHOGRAPHIC DEVICE, MICROLITHOGRAPHIC ASSIST FEATURES, SYSTEM FOR FORMING CONTACTS AND OTHER STRUCTURES AND METHOD OF DETERMINING MASK PATTERNS	12/28/2005	
6,486,956	09/816,861	US	Issued	REDUCING ASYMMETRICALLY DEPOSITED FILM INDUCED REGISTRATION ERROR	3/23/2001	11/26/2002
6,852,456	10/122,555	US	Issued	REDUCING ASYMMETRICALLY DEPOSITED FILM INDUCED REGISTRATION ERROR	4/15/2002	2/8/2005
6,795,747	10/122,786	US	Issued	REDUCING ASYMMETRICALLY DEPOSITED FILM INDUCED REGISTRATION ERROR	4/15/2002	9/21/2004
7,127,319	10/932,771	US	Issued	REDUCING ASYMMETRICALLY DEPOSITED FILM INDUCED REGISTRATION ERROR	9/2/2004	10/24/2006
		US	Abandoned	REDUCING ASYMMETRICALLY DEPOSITED FILM INDUCED REGISTRATION ERROR	8/31/2006	

6,558,477	09/688,757	US	Issued	REMOVAL OF PHOTORESIST THROUGH THE USE OF HOT DEIONIZED WATER BATH, WATER VAPOR AND OZONE GAS	10/16/2000	5/6/2003
6,622,738	10/131,371	US	Issued	APPARATUS AND SYSTEM FOR REMOVING PHOTORESIST THROUGH THE USE OF HOT DEIONIZED WATER BATH, WATER VAPOR AND OZONE GAS	4/24/2002	9/23/2003
6,707,312	09/988,987	US	Issued	PSUEDO VARIABLE RESISTOR FOR TESTER PLATFORM	11/19/2001	3/16/2004
6,376,380	09/652,601	US	Issued	METHOD OF FORMING MEMORY CIRCUITRY AND METHOD OF FORMING MEMORY CIRCUITRY COMPRISING A BURIED BIT LINE ARRAY OF MEMORY CELLS	8/30/2000	4/23/2002
7,176,109	09/816,962	US	Issued	METHOD FOR FORMING RAISED STRUCTURES BY CONTROLLED SELECTIVE EPITAXIAL GROWTH OF FACET USING SPACER	3/23/2001	2/13/2007
	10/046,497	US	Abandoned	METHOD FOR FORMING RAISED STRUCTURES BY CONTROLLED SELECTIVE EPITAXIAL GROWTH OF FACET USING SPACER	10/26/2001	
	10/379,494	US	Pending	METHOD FOR FORMING RAISED STRUCTURES BY CONTROLLED SELECTIVE EPITAXIAL GROWTH OF FACET USING SPACER	3/4/2003	
	11/512,478	US	Abandoned	METHOD FOR FORMING RAISED STRUCTURES BY CONTROLLED SELECTIVE EPITAXIAL GROWTH OF FACET USING SPACER	8/30/2006	
	11/512,574	US	Abandoned	METHOD FOR FORMING RAISED STRUCTURES BY CONTROLLED SELECTIVE EPITAXIAL GROWTH OF FACET USING SPACER	8/30/2006	
6,454,912	09/810,368	US	Issued	METHOD AND APPARATUS FOR THE FABRICATION OF FERROELECTRIC FILMS	3/15/2001	9/24/2002

6,858,120	10/217,212	US	Issued	METHOD AND APPARATUS FOR THE FABRICATION OF FERROELECTRIC FILMS	8/9/2002	2/22/2005
7,041,341	10/945,535	US	Issued	PROCESS FOR THE FABRICATION OF OXIDE FILMS	9/20/2004	5/9/2006
	11/431,404	US	Abandoned	METHOD OF FORMING A FERROELECTRIC FILM	5/9/2006	
7,160,817	09/945,393	US	Issued	DIELECTRIC MATERIAL FORMING METHODS AND ENHANCED DIELECTRIC MATERIALS	8/30/2001	1/9/2007
7,052,953	10/914,888	US	Issued	DIELECTRIC MATERIAL FORMING METHODS AND ENHANCED DIELECTRIC MATERIALS	8/9/2004	5/30/2006
	11/591,956	US	Abandoned	DIELECTRIC MATERIAL FORMING METHODS AND ENHANCED DIELECTRIC MATERIALS	11/1/2006	
6,940,328	10/229,790	US	Issued	METHODS AND APPARATUS FOR DUTY CYCLE CONTROL	8/28/2002	9/6/2005
6,429,087	09/386,537	US	Issued	METHODS OF FORMING CAPACITORS	8/30/1999	8/6/2002
6,627,938	09/729,130	US	Issued	CAPACITOR CONSTRUCTIONS	12/1/2000	9/30/2003